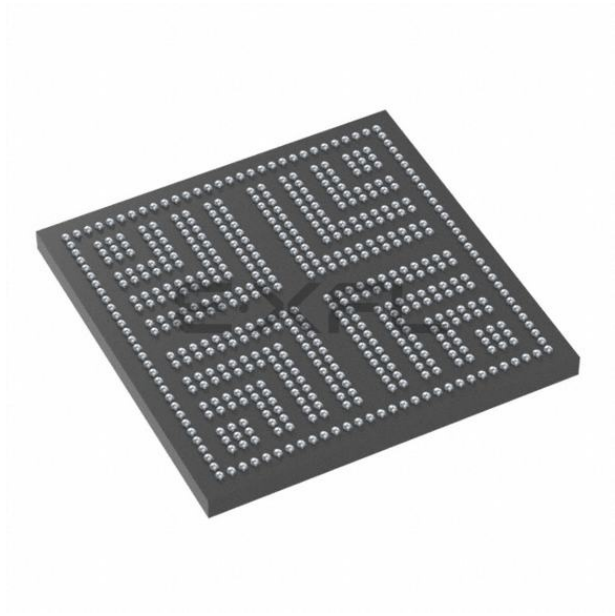

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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	300
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	536-LFBGA, CSPBGA
Supplier Device Package	536-CSPBGA (16x16)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300ts-fcsg536i

2 Overview

This datasheet describes PolarFire® FPGA device characteristics with industrial temperature range (–40 °C to 100 °C T_J) and extended commercial temperature range (0 °C to 100 °C T_J). The devices are provided with a standard speed grade (STD) and a –1 speed grade with higher performance. The FPGA core supply V_{DD} can operate at 1.0 V for lower-power or 1.05 V for higher performance. Similarly, the transceiver core supply V_{DDA} can also operate at 1.0 V or 1.05 V. Users select the core operating voltage while creating the Libero project.

The maximum overshoot duration is specified as a high-time percentage over the lifetime of the device. A DC signal is equivalent to 100% of the duty-cycle.

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for HSIO.

Table 6 • Maximum Overshoot During Transitions for HSIO

AC (V_{IN}) Overshoot Duration as % at T_J = 100 °C	Condition (V)
100	1.8
100	1.85
100	1.9
100	1.95
100	2
100	2.05
100	2.1
100	2.15
100	2.2
90	2.25
30	2.3
7.5	2.35
1.9	2.4

Note: Overshoot level is for VDDI at 1.8 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for HSIO.

Table 7 • Maximum Undershoot During Transitions for HSIO

AC (V_{IN}) Undershoot Duration as % at T_J = 100 °C	Condition (V)
100	–0.05
100	–0.1
100	–0.15
100	–0.2
100	–0.25
100	–0.3
100	–0.35
100	–0.4
44	–0.45
14	–0.5
4.8	–0.55
1.6	–0.6

The following table shows the maximum AC input voltage (V_{IN}) overshoot duration for GPIO.

Table 8 • Maximum Overshoot During Transitions for GPIO

AC (V_{IN}) Overshoot Duration as % at T_J = 100 °C	Condition (V)
100	3.8
100	3.85
100	3.9
100	3.95
70	4
50	4.05
33	4.1
22	4.15
14	4.2
9.8	4.25
6.5	4.3
4.4	4.35
3	4.4
2	4.45
1.4	4.5
0.9	4.55
0.6	4.6

Note: Overshoot level is for V_{DDI} at 3.3 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for GPIO.

Table 9 • Maximum Undershoot During Transitions for GPIO

AC (V_{IN}) Undershoot Duration as % at T_J = 100 °C	Condition (V)
100	–0.5
100	–0.55
100	–0.6
100	–0.65
100	–0.7
100	–0.75
100	–0.8
100	–0.85
100	–0.9
100	–0.95
100	–1
100	–1.05
100	–1.1
100	–1.15
100	–1.2
69	–1.25
45	–1.3

I/O Standard	Bank Type	V_{OCM}[1] Min (V)	V_{OCM} Typ (V)	V_{OCM} Max (V)	V_{OD}[2] Min (V)	V_{OD}[2] Typ (V)	V_{OD}[2] Max (V)
MLVDSE25[3]	GPIO		1.25		0.396	0.442	0.453
LVPECLE33[3]	GPIO		1.65		0.664	0.722	0.755
MIPIE25[3]	GPIO		0.25		0.1	0.22	0.3

1. V_{OCM} is the output common mode voltage.
2. V_{OD} is the output differential voltage.
3. Emulated output only.

6.3.3 Complementary Differential DC Input and Output Levels

The following tables list the complementary differential DC I/O levels.

Table 16 • Complementary Differential DC Input Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{ICM}[1,3] Min (V)	V_{ICM}[1,3] Typ (V)	V_{ICM}[1,3] Max (V)	V_{ID}[2] Min (V)	V_{ID} Max (V)
SSTL25I	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL25II	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
SSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
HSUL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
POD12I	1.14	1.2	1.26	0.787	0.840	0.895	0.1	
POD12II	1.14	1.2	1.26	0.787	0.840	0.895	0.1	

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{ICM} rules are as follows:
   a. V_{ICM} must be less than V_{DDI} -0.4V;
   b. $V_{ICM} + V_{ID}/2$ must be $<V_{DDI} + 0.4$ V;
   c. $V_{ICM} – V_{ID}/2$ must be >VSS – 0.3 V.

Standard	Description	V_L[1]	V_H[1]	V_{ID}[2]	V_{ICM}[2]	V_{MEAS}[3, 4]	V_{REF}[1, 5]	Unit
SLVS25	SLVS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V
SLVS18	SLVS 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.200	0		V
HCSL33	High-speed current steering logic (HCSL) 3.3 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
HCSL25	HCSL 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
HCSL18	HCSL 1.8 V	V_{ICM} – .125	V_{ICM} + .125	0.250	0.350	0		V
BLVDSE25[6]	Bus LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
MLVDSE25[6]	Multipoint LVDS 2.5 V	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
LVPECL33	Low-voltage positive emitter coupled logic	V_{ICM} – .125	V_{ICM} + .125	0.250	1.650	0		V
LVPECLE33[6]	Low-voltage positive emitter coupled logic	V_{ICM} – .125	V_{ICM} + .125	0.250	1.650	0		V
SSTL25I	Differential SSTL 2.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
SSTL25II	Differential SSTL 2.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	1.250	0		V
SSTL18I	Differential SSTL 1.8 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SSTL18II	Differential SSTL 1.8 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.900	0		V
SSTL15	Differential SSTL 1.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
SSTL135	Differential SSTL 1.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL15I	Differential HSTL 1.5 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL15II	Differential HSTL 1.5 V Class II	V_{ICM} – .125	V_{ICM} + .125	0.250	0.750	0		V
HSTL135I	Differential HSTL 1.35 V Class I	V_{ICM} – .125	V_{ICM} + .125	0.250	0.675	0		V

Standard	STD	–1	Unit
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with V_{ID} ≥200 mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps

7.1.5 Maximum PHY Rate for Memory Interface IP

The following tables provide information about the maximum PHY rate for memory interface IP.

Table 28 • Maximum PHY Rate for Memory Interfaces IP for HSIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR4	8:1	1.8 V	1.2 V	1333	1600	167	200
DDR3	8:1	1.8 V	1.5 V	1067	1333	133	167
DDR3L	8:1	1.8 V	1.35 V	1067	1333	133	167
LPDDR3	8:1	1.8 V	1.2 V	1067	1333	133	167
QDRII+	8:1	1.8 V	1.5 V	900	1100	112.5	137.5
RLDRAM3[1]	8:1	1.8 V	1.35 V	1067	1067	133	133
RLDRAM3[1]	4:1	1.8 V	1.35 V	667	800	167	200
RLDRAM3[1]	2:1	1.8 V	1.35 V	333	400	167	200
RLDRAM2[1]	8:1	1.8 V	1.8 V	800	1067	100	133
RLDRAM2[1]	4:1	1.8 V	1.8 V	667	800	167	200
RLDRAM2[1]	2:1	1.8 V	1.8 V	333	400	167	200

1. RLDRAM2 and RLDRAM3 are not supported with a soft IP controller currently.

Table 29 • Maximum PHY Rate for Memory Interfaces IP for GPIO Banks

Memory Standard	Gearing Ratio	V_{DDAUX}	V_{DDI}	STD (Mbps)	–1 (Mbps)	Fabric STD (MHz)	Fabric –1 (MHz)
DDR3	8:1	2.5 V	1.5 V	800	1067	100	133
QDRII+	8:1	2.5 V	1.5 V	900	900	113	113
RLDRAM2[1]	4:1	2.5 V	1.8 V	800	800	200	200
RLDRAM2[1]	2:1	2.5 V	1.8 V	400	400	200	200

1. RLDRAM2 is currently not supported with a soft IP controller.

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output F_{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F_{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance[1]	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V –1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V –1	Unit	Condition
Global clock F_{MAX}	F_{MAXG}	500	500	500	500	MHz	
Regional clock F_{MAX}	F_{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F_{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T_{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter	Symbol	Min	Typ	Max	Unit
Operating current (V_{DD18})	RC_{SCVPP}			0.1	µA
Operating current (V_{DD})	RC_{SCVDD}			60.7	µA

Parameter	Modes [1]	STD Min	STD Max	–1 Min	–1 Max	Unit
Transceiver RX_CLK range (non-deterministic PCS mode with global or regional fabric clocks)	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 4.8 Gbps		300		300	MHz
	20-bit, max data rate = 6.0 Gbps		300		300	MHz
	32-bit, max data rate = 10.3125 Gbps		325		325	MHz
	40-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		260		320	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		130		160	MHz
	Fabric pipe mode 32-bit, max data rate = 6.0 Gbps		150		150	MHz
Transceiver TX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (–STD) / 4.25 Gbps (–1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (–STD) / 5.32 Gbps (–1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (–STD) / 8.5 Gbps (–1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (–STD) / 10.6 Gbps (–1)[1]		225		266	Mhz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		130		160	MHz
Transceiver RX_CLK range (deterministic PCS mode with regional fabric clocks)	8-bit, max data rate = 1.6 Gbps		200		200	MHz
	10-bit, max data rate = 1.6 Gbps		160		160	MHz
	16-bit, max data rate = 3.6 Gbps (–STD) / 4.25 Gbps (–1)		225		266	MHz
	20-bit, max data rate = 4.5 Gbps (–STD) / 5.32 Gbps (–1)		225		266	MHz
	32-bit, max data rate = 7.2 Gbps (–STD) / 8.5 Gbps (–1)		225		266	MHz
	40-bit, max data rate = 9.0 Gbps (–STD) / 10.6 Gbps (–1)[1]		225		266	MHz
	64-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		165		200	MHz
	80-bit, max data rate = 10.3125 Gbps (–STD) / 12.7 Gbps (–1)[1]		130		160	MHz

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

Note: Until specified, all modes are non-deterministic. For more information, see UG0677: PolarFire FPGA Transceiver User Guide.

5. Improved jitter characteristics for a specific industry standard are possible in many cases due to improved reference clock or higher V_{CO} rate used.
6. Tx jitter is specified with all transmitters on the device enabled, a 10–12-bit error rate (BER) and Tx data pattern of PRBS7.
7. From the PMA mode, the TX_ELEC_IDLE port to the XVCR TXP/N pins.
   FTxRefClk = 75 MHz with typical settings.
   For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6). (see page 6)

7.4.6 Receiver Performance

The following table describes performance of the receiver.

Table 53 • PolarFire Transceiver Receiver Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input voltage range	V_{IN}	0		V_{DDA} + 0.3	V	
Differential peak-to-peak amplitude	V_{IDPP}	140		1250	mV	
Differential termination	V_{ITERM}		85		Ω	
	V_{ITERM}		100		Ω	
	V_{ITERM}		150		Ω	
Common mode voltage	V_{ICMDC} [1]	0.7 × V_{DDA}		0.9 × V_{DDA}	V	DC coupled
Exit electrical idle detection time	T_{EIDET}		50	100	ns	
Run length of consecutive identical digits (CID)	C_{ID}			200	UI	
CDR PPM tolerance[2]	C_{DRPPM}			1.15	% UI	
CDR lock-to-data time	T_{LTD}				CDR_{REFCLK} UI	
CDR lock-to-ref time	T_{LTF}				CDR_{REFCLK} UI	
Loss-of-signal detect (Peak Detect Range setting = high)[9]	$V_{DETLHIGH}$				mV	Setting = 1
	$V_{DETLHIGH}$				mV	Setting = 2
	$V_{DETLHIGH}$				mV	Setting = 3
	$V_{DETLHIGH}$				mV	Setting = 4
	$V_{DETLHIGH}$				mV	Setting = 5
	$V_{DETLHIGH}$				mV	Setting = 6
	$V_{DETLHIGH}$				mV	Setting = 7
Loss-of-signal detect (Peak Detect Range setting = low)[9]	V_{DETLOW}	65		175	mV	Setting = PCIe[3,7]
	V_{DETLOW}	95		190	mV	Setting = SATA[4,8]
	V_{DETLOW}	75		170	mV	Setting = 1
	V_{DETLOW}	95		185	mV	Setting = 2
	V_{DETLOW}	100		190	mV	Setting = 3
	V_{DETLOW}	140		210	mV	Setting = 4
	V_{DETLOW}	155		240	mV	Setting = 5
	V_{DETLOW}	165		245	mV	Setting = 6
	V_{DETLOW}	170		250	mV	Setting = 7
Sinusoidal jitter tolerance	T_{SJTOL}				UI	>8.5 Gbps – 12.7 Gbps [5, 10]

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	33.2	34.9	µs
	MPF300T, TL, TS, TLS	33.2	34.9	µs
	MPF500T, TL, TS, TLS			µs
Factory digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	493.6	510.1	µs
	MPF300T, TL, TS, TLS	493.6	510.1	µs
	MPF500T, TL, TS, TLS			µs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6 Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable)[1, 4]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF500T, TL, TS, TLS						

Notes:

- FlashPro4 4 MHz TCK.
- FlashPro5 10 MHz TCK.
- PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

Table 83 • Verify System Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
In application verify by index	$T_{IAP\_Ver\_Index}$	44H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s
In application verify by SPI address	$T_{IAP\_Ver\_Addr}$	45H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s

7.6.8 Authentication Time

The following tables describe authentication system service time.

Table 84 • Authentication Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
Bitstream Authentication	T_{BIT_AUTH}	22H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			s
IAP Image Authentication	T_{IAP_AUTH}	23H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			

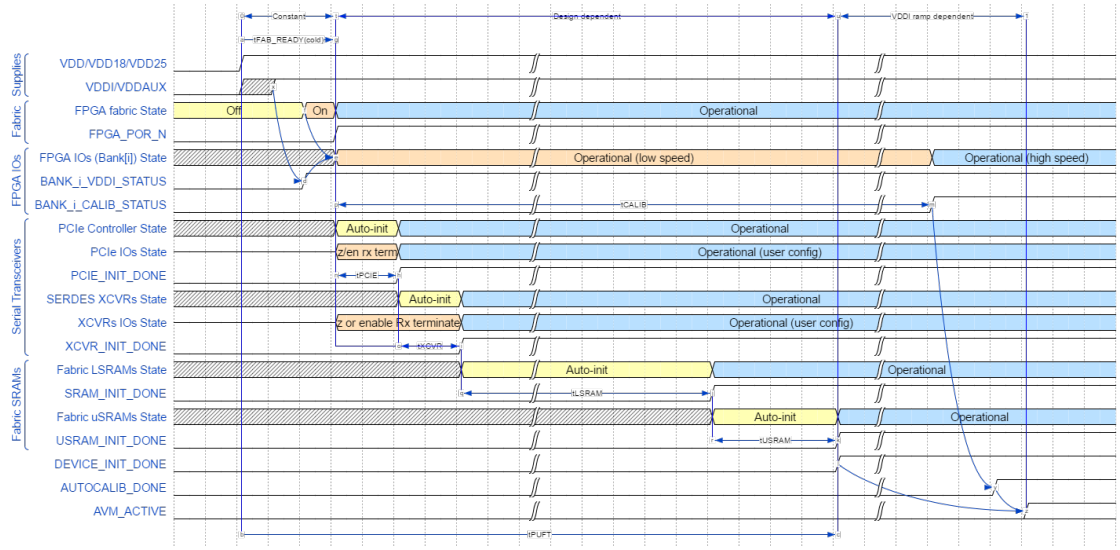
7.6.9 Secure NVM Performance

The following table describes secure NVM performance.

Table 85 • sNVM Read/Write Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Plain text programming		7.0	7.2	7.9	ms	
Authenticated text programming		7.2	7.4	9.4	ms	
Authenticated and encrypted text programming		7.2	7.4	9.4	ms	
Authentication R/W 1st access from power-up overhead	T_{PUF_OVHD}		100	111	ms	From T_{FAB_READY}
Plain text read		7.67	7.79	8.2	µs	

Figure 5 • Cold Reset Timing



Notes:

- The previous diagram showsthe case where VDDI/VDDAUX of I/O banks are powered either before or sufficiently soon after VDD/VDD18/VDD25 that the I/O bank enable time is measured from the assertion time of VDD/VDD18/VDD25 (that is, the PUFT specification). If VDDI/VDDAUX of I/O banks are powered sufficiently after VDD/VDD18/VDD25, then the I/O bank enable time is measured from the assertion of VDDI/VDDAUX and is not specified by the PUFT specification. In this case, I/O operation is indicated by the assertion of BANK_i_VDDI_STATUS, rather than being measured relative to FABRIC_POR_N negation.
- AUTOCALIB_DONE assertion indicates the completion of calibration for any I/O banks specified by the user for auto-calibration. AUTOCALIB_DONE asserts independently of DEVICE_INIT_DONE. It may assert before or after DEVICE_INIT_DONE and is determined by the following:
  - How long after VDD/VDD18/VDD25 that VDDI/VDDAUX are powered on. Note that if any of the user-specified I/O banks are not powered on within the auto-calibration timeout window, then AUTOCALIB_DONE doesn't assert until after this timeout.
  - The specified ramp times of VDDI of each I/O bank designated for auto-calibration.
  - How much auto-initialization is to be performed for the PCIe, SERDES transceivers, and fabric LSRAMs.
- If any of the I/O banks specified for auto-calibration do not have their VDDI/VDDAUX powered on within the auto-calibration timeout window, then it will be approximately auto-calibrated whenever VDDI/VDDAUX is subsequently powered on. To obtain an accurate calibration however, on such IO banks, it is necessary to initiate a re-calibration (using CALIB_START from fabric).
- AVM_ACTIVE only asserts if avionics mode is being used. It is asserted when the later of DEVICE_INIT_DONE or AUTOCALIB_DONE assert.

7.9.2 Warm Reset Initialization Sequence

The following warm reset timing diagram shows the initialization sequencing of the device when either DEVRST_N or TAMPER_RESET_DEVICE signals are asserted.

Table 101 • Cold and Warm Boot

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from T_{FAB_READY} to ready to program through JTAG/SPI-Slave		0	0	0	ms	
The time from T_{FAB_READY} to auto-update start			T_{PUF_OVHD}[1]	T_{PUF_OVHD}[1]	ms	
The time from T_{FAB_READY} to programming recovery start			T_{PUF_OVHD}[1]	T_{PUF_OVHD}[1]	ms	
The time from T_{FAB_READY} to the tamper flags being available	T_{TAMPER_READY}	0	0	0	ms	
The time from T_{FAB_READY} to the Athena Crypto co-processor being available (for S devices only)	T_{CRYPTO_READY}	0	0	0	ms	

1. Programming depends on the PUF to power up. Refer to T_{PUF_OVHD} at section Secure NVM Performance (see page 58).

7.9.8 I/O Calibration

The following tables specify the initial I/O calibration time for the fastest and slowest supported VDDI ramp times of 0.2 ms to 50 ms, respectively. This only applies to I/O banks specified by the user to be auto-calibrated.

Table 102 • I/O Initial Calibration Time (TCALIB)

Ramp Time	Min (ms)	Max (ms)	Condition
0.2 ms	0.98	2.63	Applies to HSIO and GPIO banks
50 ms	41.62	62.19	Applies to HSIO and GPIO banks

Notes:

- The user may specify any VDDI ramp time in the range specified above. The nominal initial calibration time is given by the specified VDDI ramp time plus 2 ms.
- In order for IO calibration to start, VDDI and VDDAUX of the I/O bank must be higher than the trip point levels specified in I/O-Related Supplies (see page 66).

Table 103 • I/O Fast Recalibration Time (TRECALIB)

I/O Type	Min (ms)	Typ (ms)	Max (ms)	Condition
GPIO bank	0.16	0.20	0.24	GPIO configured for 3.3 V operation
HSIO bank	0.20	0.25	0.30	HSIO configured for 1.8 V operation

Note: In order to obtain fast re-calibration, the user must assert the relevant clock request signal from the FPGA fabric to the I/O bank controller.

The following table describes the time to enter Flash*Freeze Mode and to exit Flash*Freeze mode.

Table 104 • Flash*Freeze

Parameter	Symbol	Min	Typ	Max	Unit	Condition
The time from Flash*Freeze entry command to the Flash*Freeze state	T_{FF_ENTRY}		59		µs	
The time from Flash*Freeze exit pin assertion to fabric operational state	$T_{FF\_FABRIC\_UP}$		133		µs	
The time from Flash*Freeze exit pin assertion to I/Os operational	$T_{FF\_IO\_ACTIVE}$		143		µs	

7.10 Dedicated Pins

The following section describes the dedicated pins.

7.10.1 JTAG Switching Characteristics

The following table describes characteristics of JTAG switching.

Table 105 • JTAG Electrical Characteristics

Symbol	Description	Min	Typ	Max	Unit	Condition
T_{DISU}	TDI input setup time	0.0			ns	
T_{DIHD}	TDI input hold time	2.0			ns	
T_{TMSSU}	TMS input setup time	1.5			ns	
T_{TMSHD}	TMS input hold time	1.5			ns	
F_{TCK}	TCK frequency			25	MHz	
T_{TCKDC}	TCK duty cycle	40		60	%	
T_{TDOCQ}	TDO clock to Q out			8.4	ns	C_{LOAD} = 40 pf
T_{RSTBCQ}	TRSTB clock to Q out			23.5	ns	C_{LOAD} = 40 pf
T_{RSTBPW}	TRSTB min pulse width	50			ns	
$T_{RSTBREM}$	TRSTB removal time	0.0			ns	
$T_{RSTBREC}$	TRSTB recovery time	12.0			ns	
CIN_{TDI}	TDI input pin capacitance			5.3	pf	
CIN_{TMS}	TMS input pin capacitance			5.3	pf	
CIN_{TCK}	TCK input pin capacitance			5.3	pf	
CIN_{TRSTB}	TRSTB input pin capacitance			5.3	pf	

7.10.2 SPI Switching Characteristics

The following tables describe characteristics of SPI switching.

Table 106 • SPI Master Mode (PolarFire Master) During Programming

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{MSCK}			20	MHz	

Table 107 • SPI Master Mode (PolarFire Master) During Device Initialization

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{MSCK}			40	MHz	

Table 108 • SPI Slave Mode (PolarFire Slave)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
SCK frequency	F_{SSCK}			80	MHz	

7.10.3 SmartDebug Probe Switching Characteristics

The following table describes characteristics of SmartDebug probe switching.

Table 109 • SmartDebug Probe Performance Characteristics

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V – 1	Unit
Maximum frequency of probe signal	F_{MAX}	100	100	100	100	MHz
Minimum delay of probe signal	T_{Min_delay}	13	12	13	12	ns
Maximum delay of probe signal	T_{Max_delay}	13	12	13	12	ns

7.10.4 DEVRST_N Switching Characteristics

The following table describes characteristics of DEVRST_N switching.

Table 110 • DEVRST_N Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
DEVRST_N ramp rate	DR_{RAMP}		10		µs	It must be a normal clean digital signal, with typical rise and fall times
DEVRST_N assert time	DR_{ASSERT}	1			µs	The minimum time for DEVRST_N assertion to be recognized
DEVRST_N de-assert time	$DR_{DEASSERT}$	2.75			ms	The minimum time DEVRST_N needs to be de-asserted before assertion

7.10.5 FF_EXIT Switching Characteristics

The following table describes characteristics of FF_EXIT switching.

Table 111 • FF_EXIT Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
FF_EXIT_N ramp rate	FF_{RAMP}		10		µs	
Minimum FF_EXIT_N assert time	FF_{ASSERT}	1			µs	The minimum time for FF_EXIT_N to be recognized
Minimum FF_EXIT_N de-assert time	$FF_{DEASSERT}$	170			µs	The minimum time FF_EXIT_N needs to be de-asserted before assertion

SigVer, DSA-2048/SHA-256	1024	9810527	10884
	8K	9597000	10719
Key Agreement (KAS), DH-3072 (p=3072, security=256)		4920705	9338
Key Agreement (KAS), DH-3072 (p=3072, security=256)[1]		78914533	9083

1. With DPA counter measures.

Table 122 • NRBG

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
Instantiate: strength, s=256, 384-bit nonce, 384-bit personalization string		18221	2841
Reseed: no additional input, s=256		13585	1180
Reseed: 384-bit additional input, s=256		15922	1342
Generate: (no additional input), prediction resistance enabled, s= 256	128	15262	1755
	8K	27169	8223
Generate: (no additional input), prediction resistance disabled, s= 256	128	2138	1167
	8K	14045	8223
Generate: (384-bit additional input), prediction resistance enabled, s= 256	128	21299	1944
	8K	33206	8949
Generate: (384-bit additional input), prediction resistance disabled, s= 256	128	11657	1894
	8K	23564	8950
Un-instantiate		761	666

1. With DPA counter measures.

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